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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg332f256-qfp64t

available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.26 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG332 to keep track of time and retain data, even if the main power source should drain out.

2.1.27 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.28 General Purpose Input/Output (GPIO)

In the EFM32WG332, there are 50 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

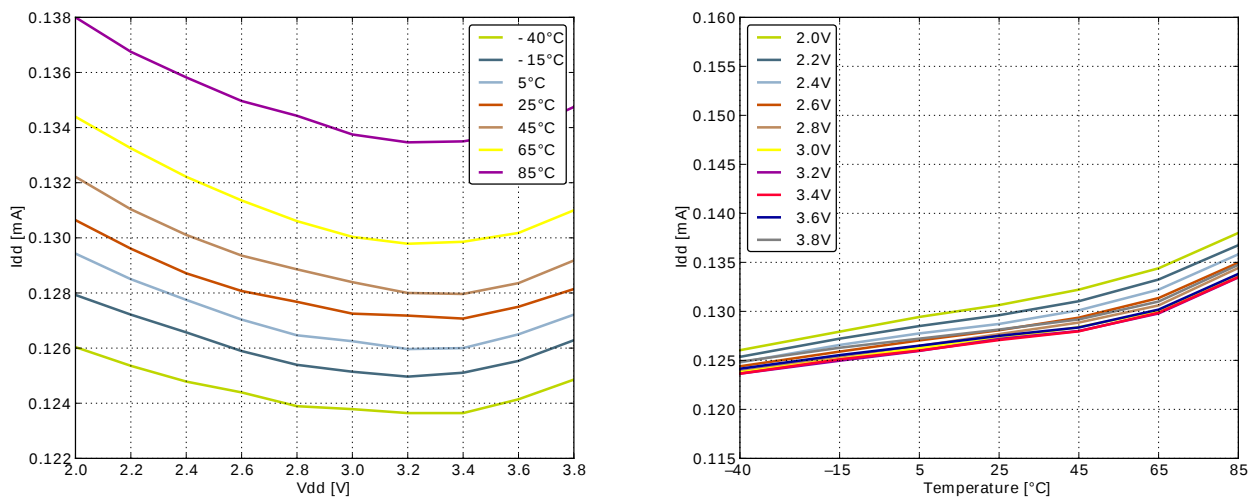
2.2 Configuration Summary

The features of the EFM32WG332 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

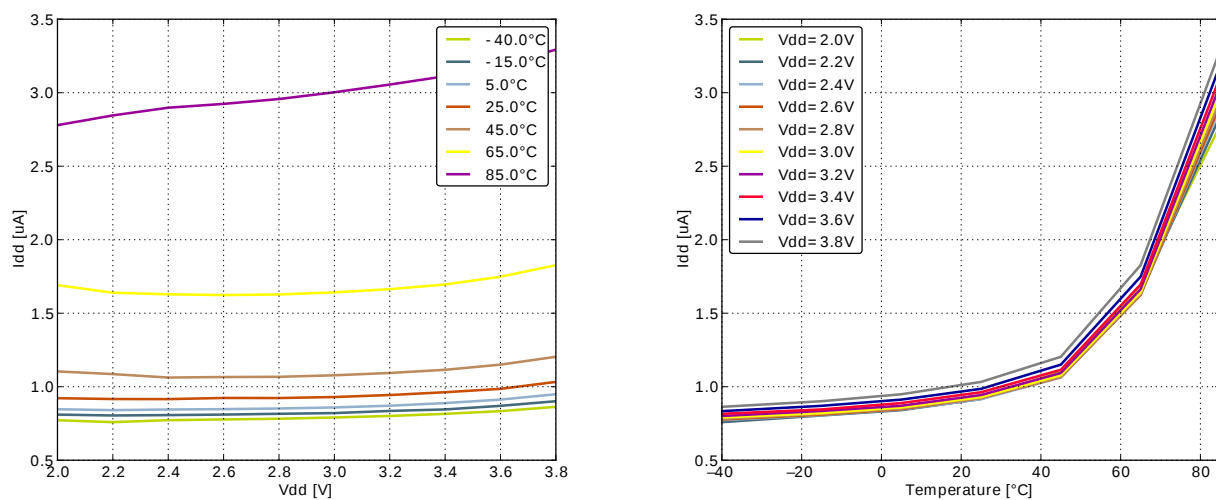
Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
USB	Full configuration	USB_VBUS, USB_VBUSEN, USB_VREGI, USB_VREGO, USB_DM, USB_DMPU, USB_DP, USB_ID

Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 1.2MHz

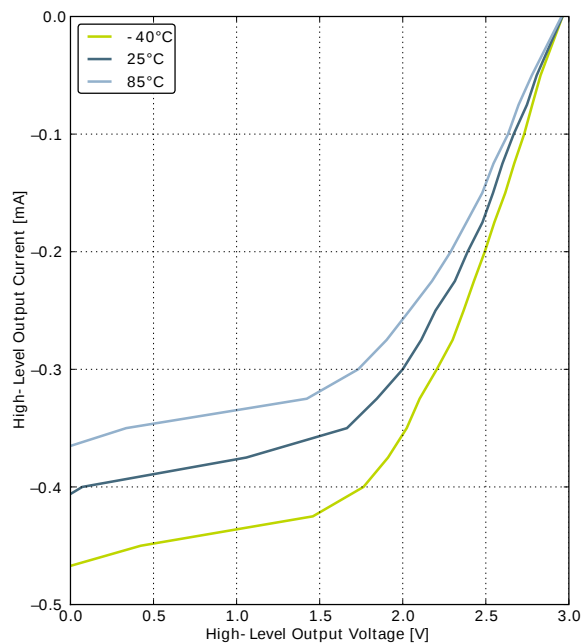


3.4.2 EM2 Current Consumption

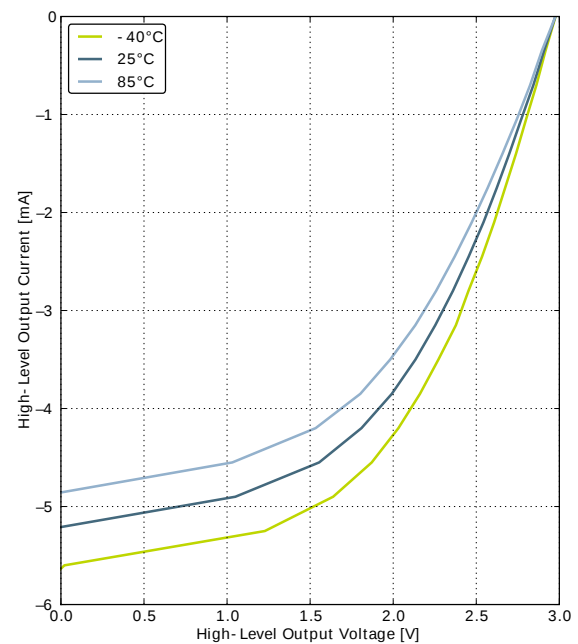
Figure 3.8. EM2 current consumption. RTC¹ prescaled to 1kHz, 32.768 kHz LFRCO.



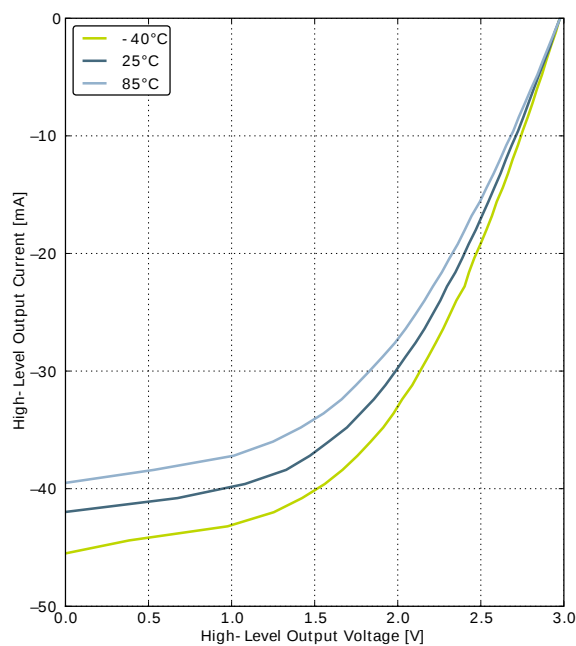
¹Using backup RTC.

Figure 3.14. Typical High-Level Output Current, 3V Supply Voltage

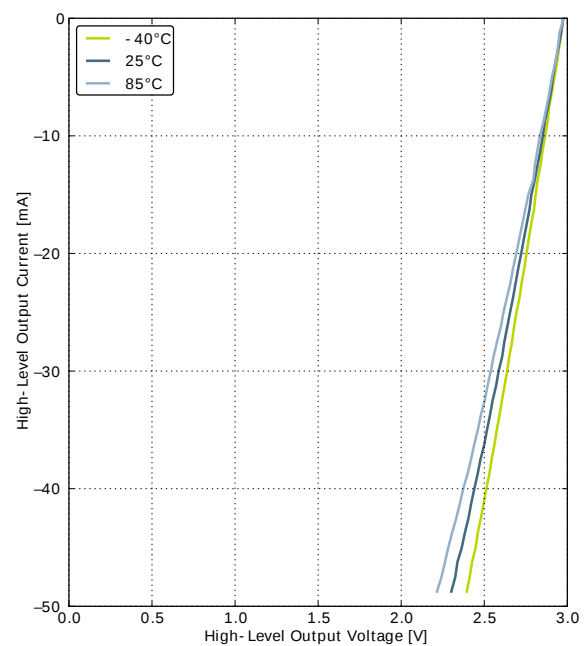
GPIO_Px_CTRL DRIVEMODE = LOWEST



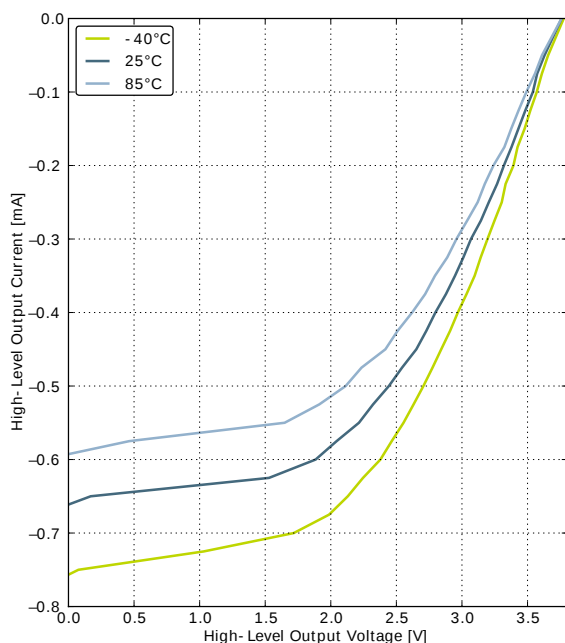
GPIO_Px_CTRL DRIVEMODE = LOW



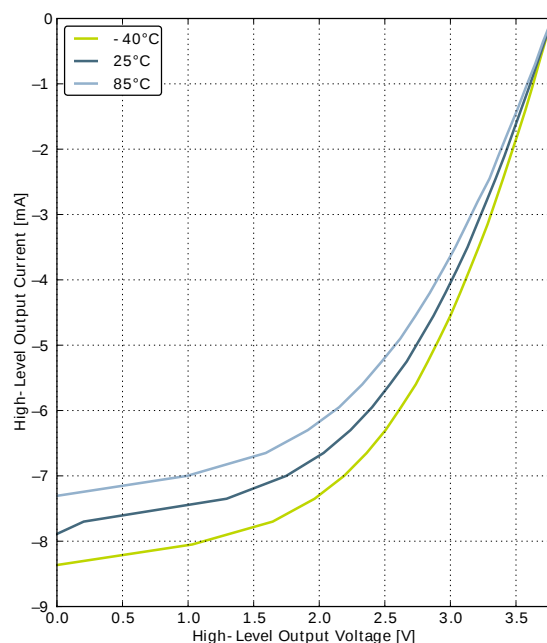
GPIO_Px_CTRL DRIVEMODE = STANDARD



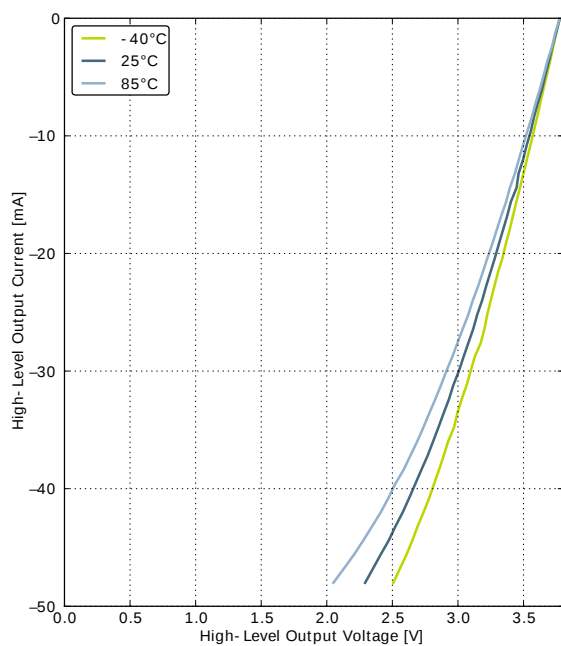
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.16. Typical High-Level Output Current, 3.8V Supply Voltage

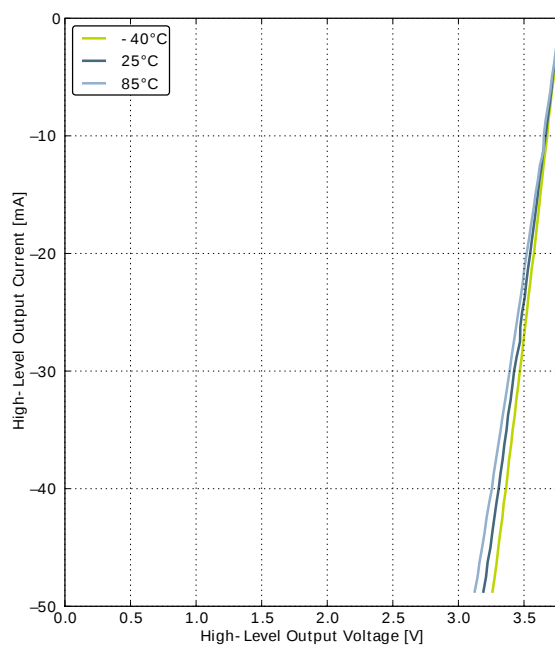
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



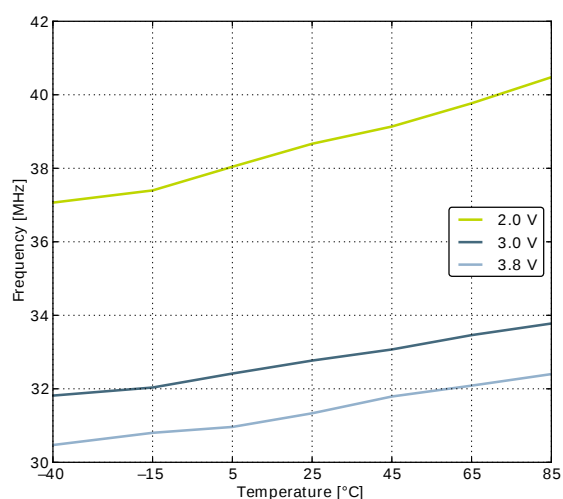
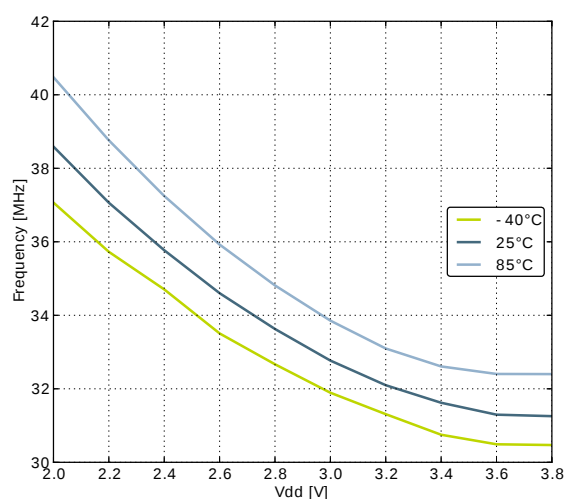
GPIO_Px_CTRL DRIVEMODE = HIGH

3.9.3 LFRCO

Table 3.11. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300		nA
TUNESTEP _{LFRCO}	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.17. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.12. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{\text{HFRCO_settling}}$	Settling time after start-up	$f_{\text{HFRCO}} = 14 \text{ MHz}$		0.6		Cycles
I_{HFRCO}	Current consumption	$f_{\text{HFRCO}} = 28 \text{ MHz}$		165	215	μA
		$f_{\text{HFRCO}} = 21 \text{ MHz}$		134	175	μA
		$f_{\text{HFRCO}} = 14 \text{ MHz}$		106	140	μA
		$f_{\text{HFRCO}} = 11 \text{ MHz}$		94	125	μA
		$f_{\text{HFRCO}} = 6.6 \text{ MHz}$		77	105	μA
		$f_{\text{HFRCO}} = 1.2 \text{ MHz}$		25	40	μA
DC_{HFRCO}	Duty cycle	$f_{\text{HFRCO}} = 14 \text{ MHz}$	48.5	50	51	%
$\text{TUNESTEP}_{\text{HFRCO}}$	Frequency step for LSB change in TUNING value			0.3^1		%

¹The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

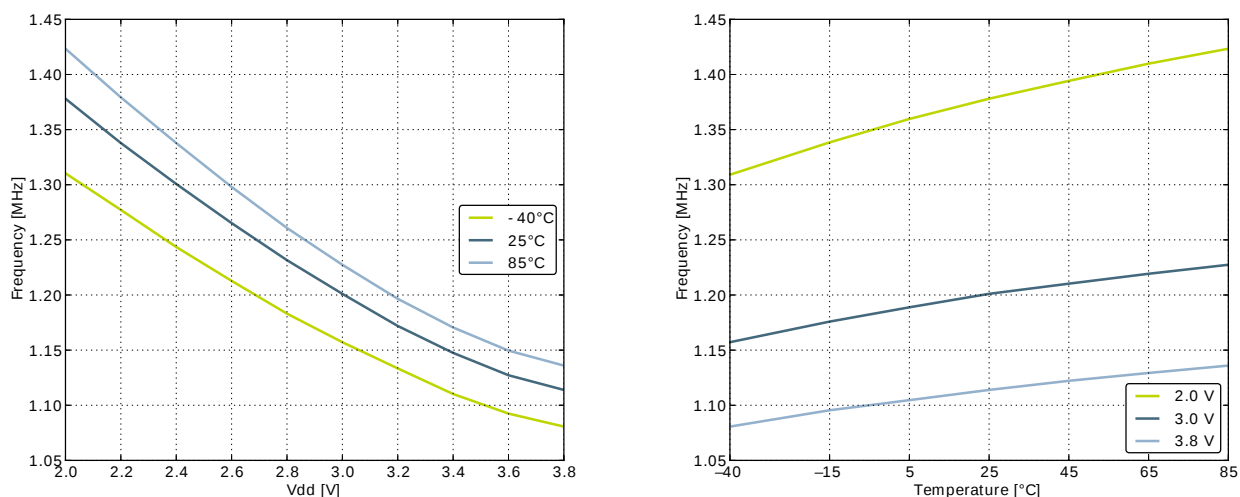
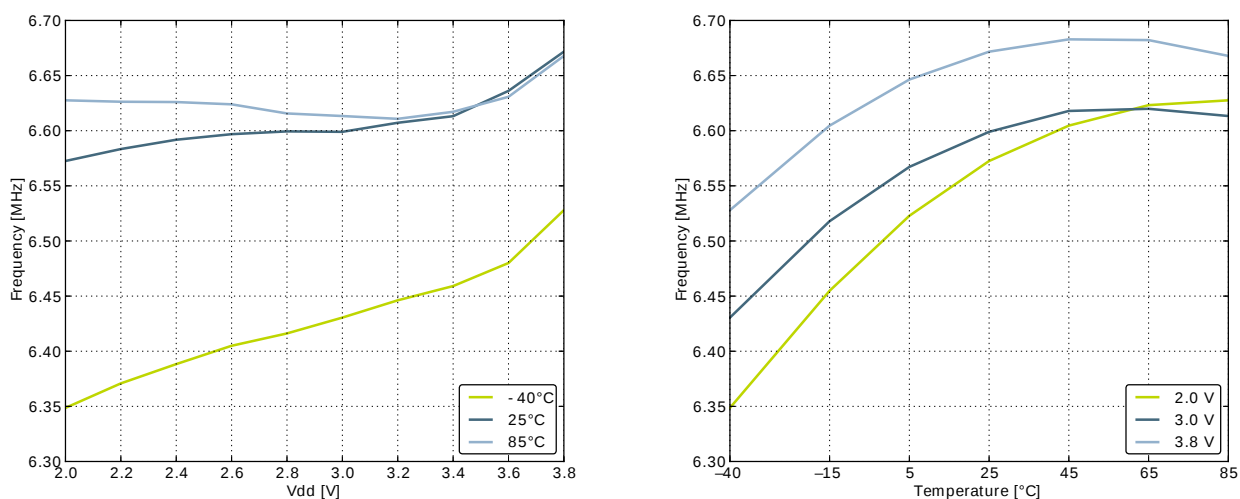
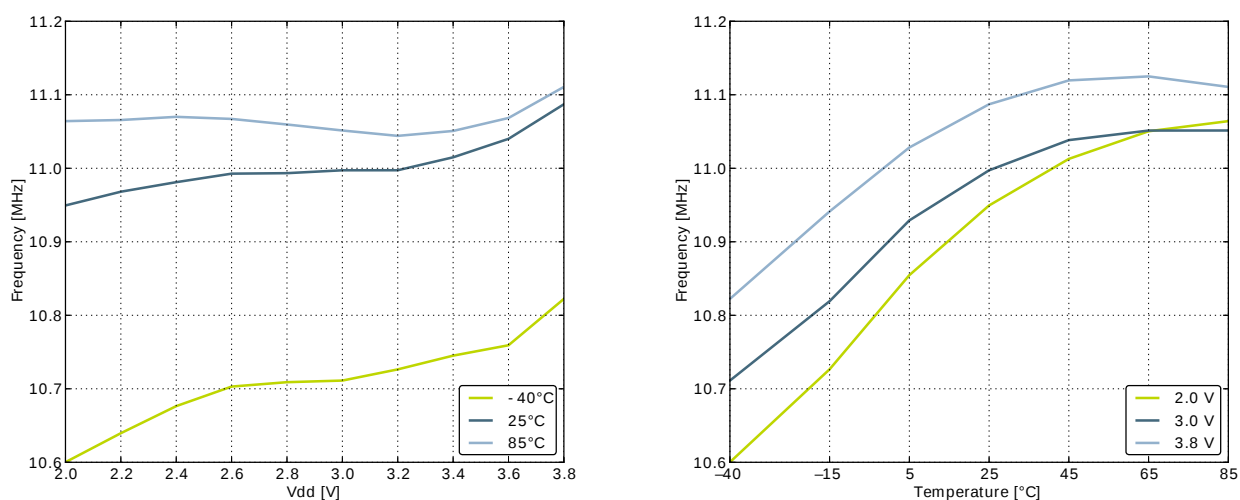
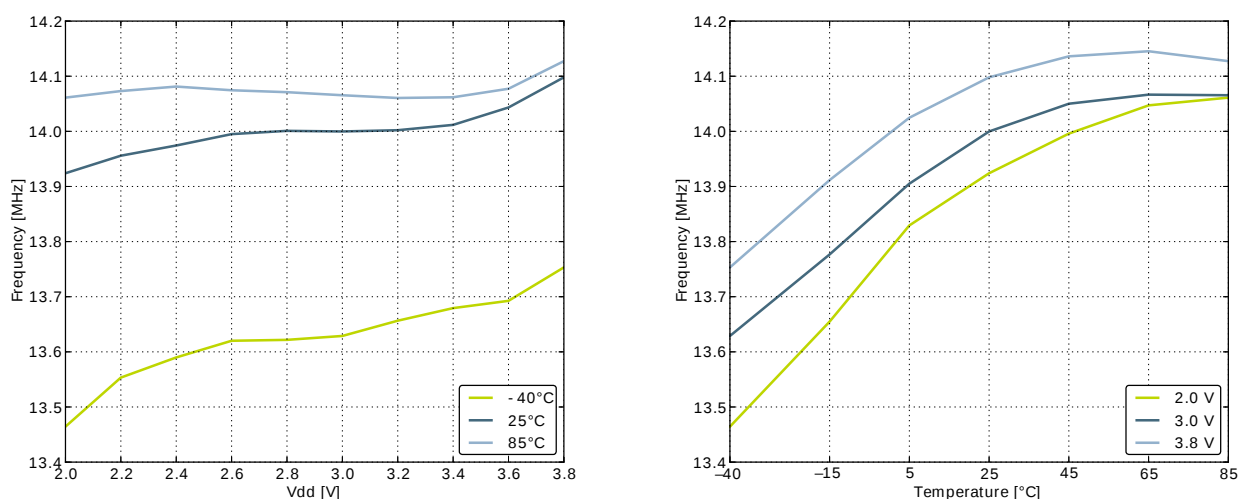


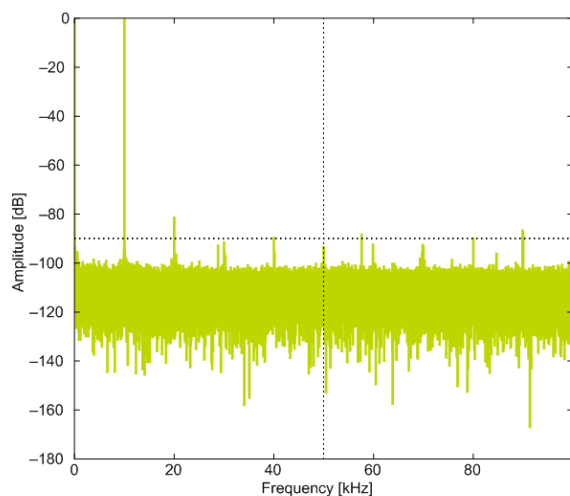
Figure 3.19. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.20. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature****Figure 3.21. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	reference voltage on channel 6					
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
I _{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		μA
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MΩ
R _{ADCFLT}	Input RC filter resistance			10		kΩ
C _{ADCFLT}	Input RC filter/decoupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator			5		μs

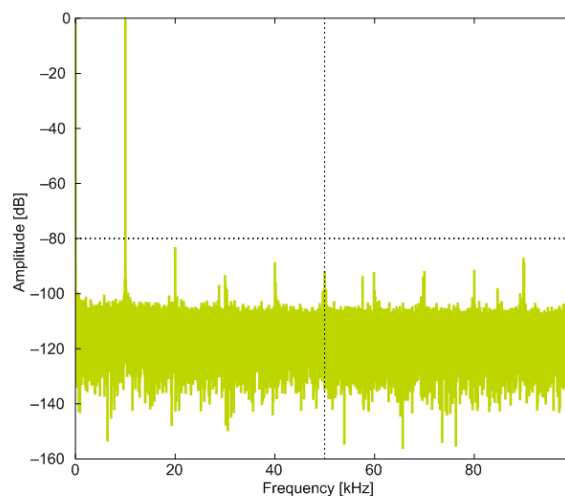
Symbol	Parameter	Condition	Min	Typ	Max	Unit
	and ADC core in NORMAL mode					
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V _{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		70		dB
SINAD _{ADC}	Signal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB

3.10.1 Typical performance

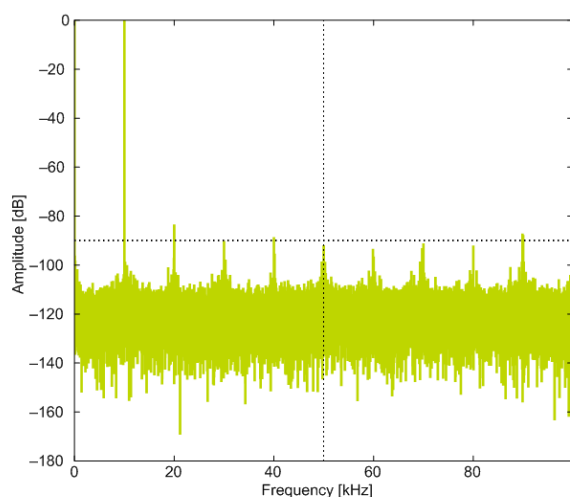
Figure 3.26. ADC Frequency Spectrum, $V_{dd} = 3V$, Temp = 25°C



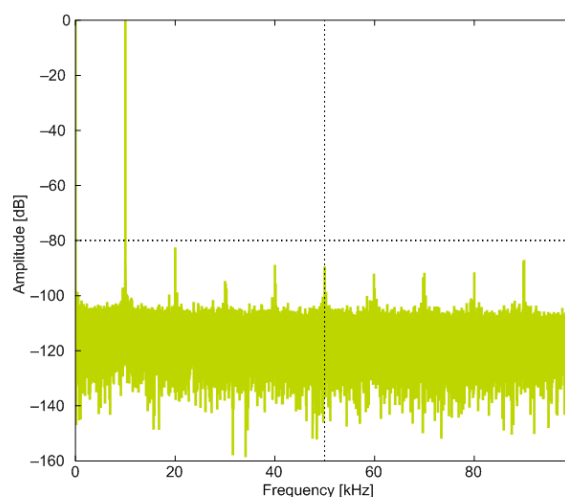
1.25V Reference



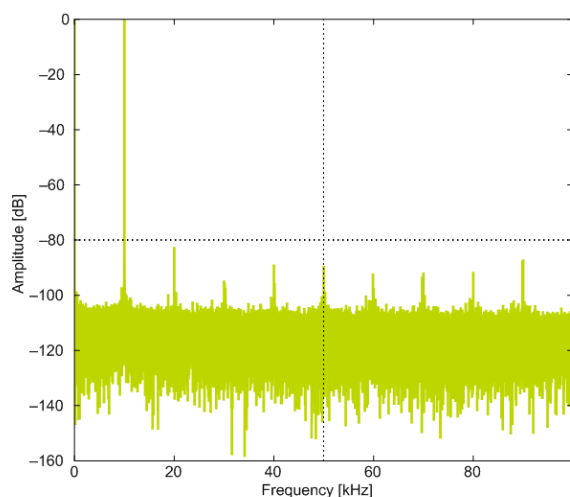
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

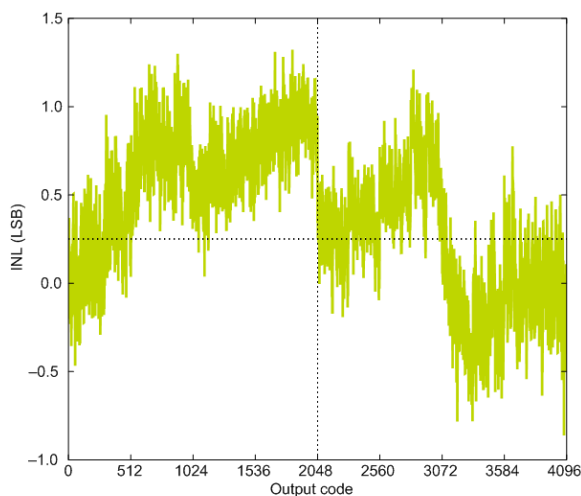
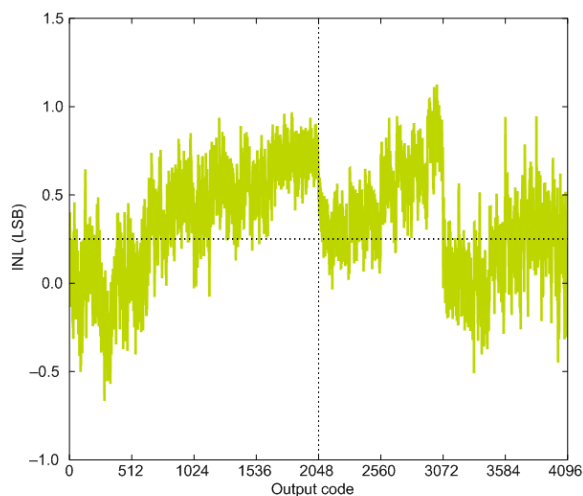
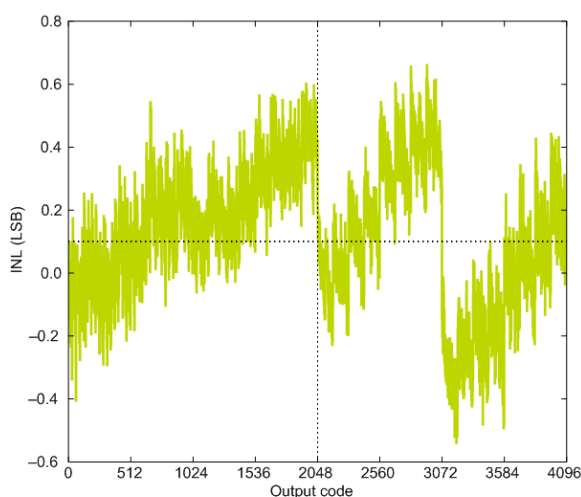
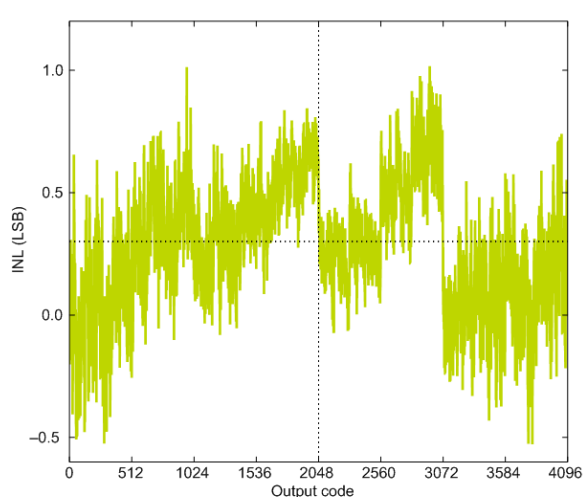
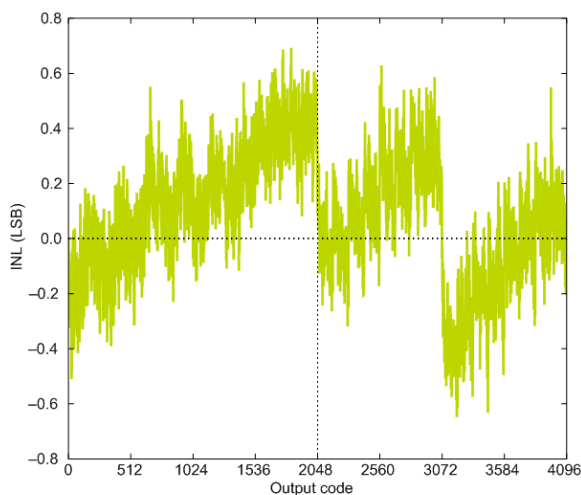
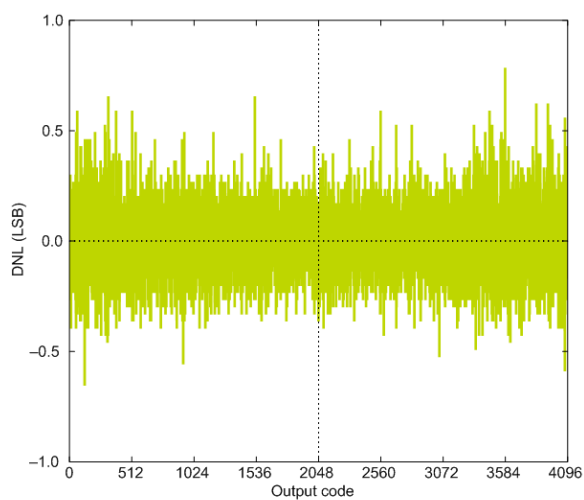
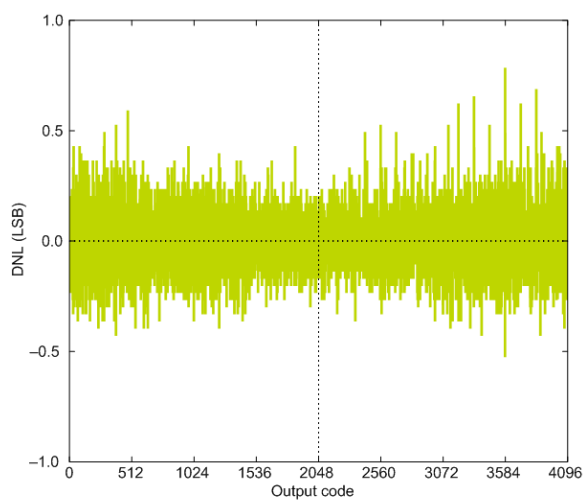
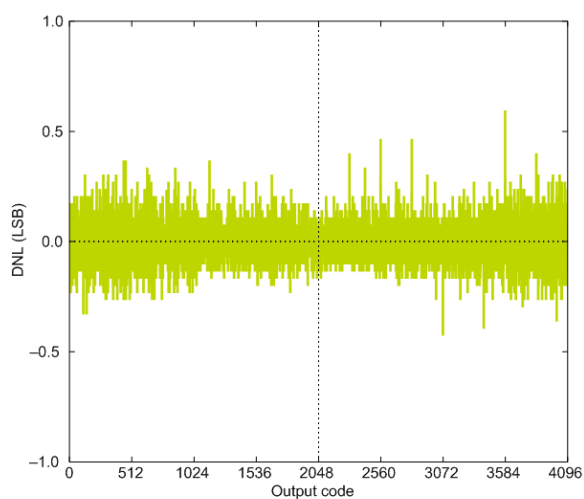
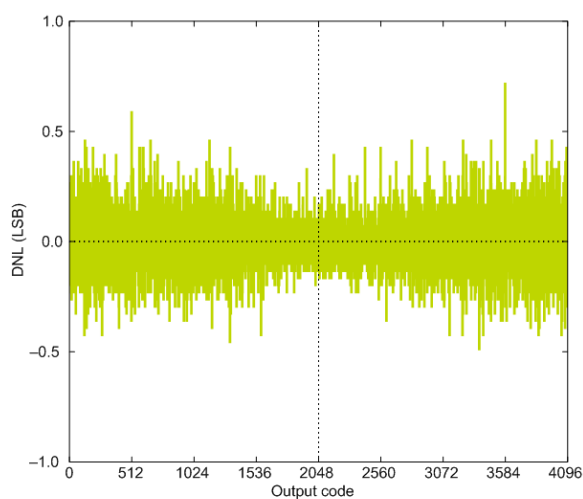
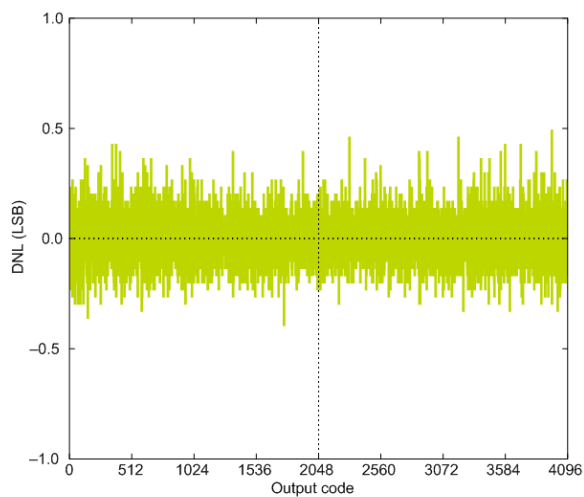
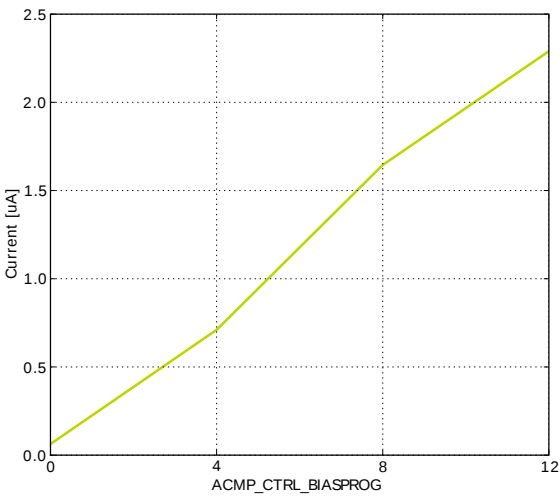
Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

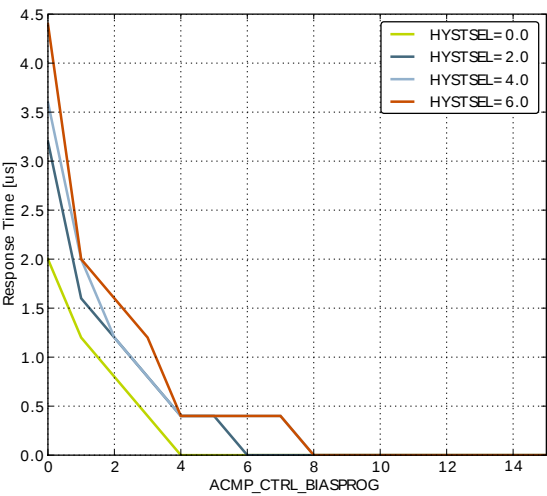
Figure 3.28. ADC Differential Linearity Error vs Code, V_{dd} = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	μA
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C _L =75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V
		OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <V _{in} <V _{DD} , OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V _{SS} <V _{in} <V _{DD} -1.2, OPAxHCMDIS=1		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/μs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/μs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/μs
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}

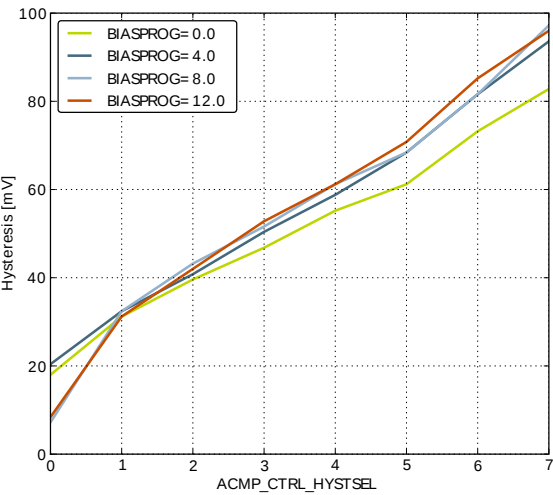
Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



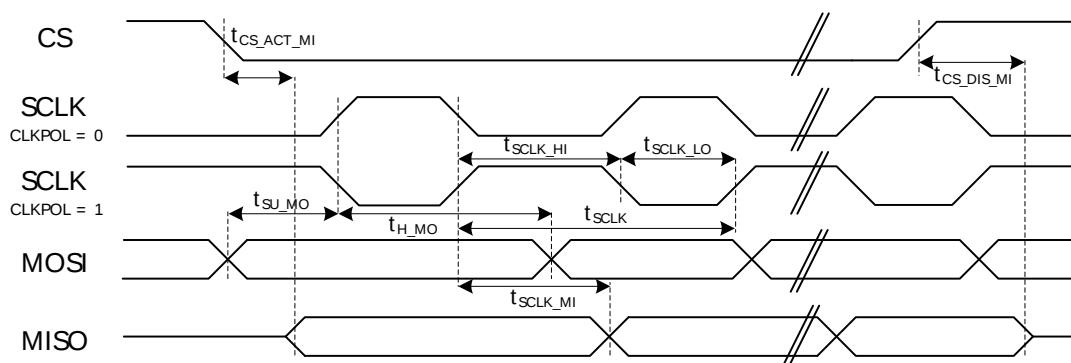
Current consumption, HYSTSEL = 4



Response time



Hysteresis

Figure 3.39. SPI Slave Timing**Table 3.25. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{1\ 2}$	SCKL period	$6 * t_{HFPER-CLK}$			ns
$t_{SCLK_hi}^{1\ 2}$	SCLK high period	$3 * t_{HFPER-CLK}$			ns
$t_{SCLK_lo}^{1\ 2}$	SCLK low period	$3 * t_{HFPER-CLK}$			ns
$t_{CS_ACT_MI}^{1\ 2}$	CS active to MISO	5.00		35.00	ns
$t_{CS_DIS_MI}^{1\ 2}$	CS disable to MISO	5.00		35.00	ns
$t_{SU_MO}^{1\ 2}$	MOSI setup time	5.00			ns
$t_{H_MO}^{1\ 2}$	MOSI hold time	$2 + 2 * t_{HF-CLK}$			ns
$t_{SCLK_MI}^{1\ 2}$	SCLK to MISO	$7 + t_{HFPER-CLK}$		$42 + 2 * t_{HFPERCLK}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.26. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{12}$	SCKL period	$6 * t_{HFPER-CLK}$			ns
$t_{SCLK_hi}^{12}$	SCLK high period	$3 * t_{HFPER-CLK}$			ns
$t_{SCLK_lo}^{12}$	SCLK low period	$3 * t_{HFPER-CLK}$			ns
$t_{CS_ACT_MI}^{12}$	CS active to MISO	5.00		35.00	ns
$t_{CS_DIS_MI}^{12}$	CS disable to MISO	5.00		35.00	ns
$t_{SU_MO}^{12}$	MOSI setup time	5.00			ns
$t_{H_MO}^{12}$	MOSI hold time	$2 + 2 * t_{HF-CLK}$			ns

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_MI}}^{12}$	SCLK to MISO	$-264 + t_{\text{HF-}}^{\text{PERCLK}}$		$-234 + 2 * t_{\text{HFPERCLK}}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

3.17 Digital Peripherals

Table 3.27. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		4.0		$\mu\text{A}/\text{MHz}$
I_{UART}	UART current	UART idle current, clock enabled		3.8		$\mu\text{A}/\text{MHz}$
I_{LEUART}	LEUART current	LEUART idle current, clock enabled		194.0		nA
I_{I2C}	I2C current	I2C idle current, clock enabled		7.6		$\mu\text{A}/\text{MHz}$
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.5		$\mu\text{A}/\text{MHz}$
I_{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		85.8		nA
I_{PCNT}	PCNT current	PCNT idle current, clock enabled		91.4		nA
I_{RTC}	RTC current	RTC idle current, clock enabled		54.6		nA
I_{AES}	AES current	AES idle current, clock enabled		1.8		$\mu\text{A}/\text{MHz}$
I_{GPIO}	GPIO current	GPIO idle current, clock enabled		3.4		$\mu\text{A}/\text{MHz}$
I_{PRS}	PRS current	PRS idle current		3.9		$\mu\text{A}/\text{MHz}$
I_{DMA}	DMA current	Clock enable		10.9		$\mu\text{A}/\text{MHz}$

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
HFX TAL_P	PB13							High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7	PC7		PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6	PC6		PC0	PF0	PE12	I2C0 Serial Data input / output.
I2C1_SCL	PC5							I2C1 Serial Clock Line input / output.
I2C1_SDA	PC4	PB11						I2C1 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exit output 0.
LES_ALTEX1	PD7							LESENSE alternate exit output 1.
LES_ALTEX2	PA3							LESENSE alternate exit output 2.
LES_ALTEX3	PA4							LESENSE alternate exit output 3.
LES_ALTEX4	PA5							LESENSE alternate exit output 4.
LES_ALTEX5	PE11							LESENSE alternate exit output 5.
LES_ALTEX6	PE12							LESENSE alternate exit output 6.
LES_ALTEX7	PE13							LESENSE alternate exit output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH2	PC2							LESENSE channel 2.
LES_CH3	PC3							LESENSE channel 3.
LES_CH4	PC4							LESENSE channel 4.
LES_CH5	PC5							LESENSE channel 5.
LES_CH6	PC6							LESENSE channel 6.
LES_CH7	PC7							LESENSE channel 7.
LES_CH8	PC8							LESENSE channel 8.
LES_CH9	PC9							LESENSE channel 9.
LES_CH10	PC10							LESENSE channel 10.
LES_CH11	PC11							LESENSE channel 11.
LETIM0_OUT0	PD6	PB11	PF0	PC4				Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7		PF1	PC5				Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14	PE15	PF1	PA0			LEUART0 Receive input.
LEU0_TX	PD4	PB13	PE14	PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LEU1_RX	PC7							LEUART1 Receive input.
LEU1_TX	PC6	PA5						LEUART1 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7							Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN			PC0	PD6				Pulse Counter PCNT0 input number 0.
PCNT0_S1IN			PC1	PD7				Pulse Counter PCNT0 input number 1.
PCNT1_S0IN	PC4							Pulse Counter PCNT1 input number 0.
PCNT1_S1IN	PC5							Pulse Counter PCNT1 input number 1.
PCNT2_S0IN	PD0	PE8						Pulse Counter PCNT2 input number 0.
PCNT2_S1IN	PD1	PE9						Pulse Counter PCNT2 input number 1.
PRS_CH0	PA0							Peripheral Reflex System PRS, channel 0.

7 Revision History

7.1 Revision 1.40

June 13th, 2014

Removed "Preliminary" markings.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Added AUXHFRCO to blockdiagram and electrical characteristics.

Updated current consumption data.

Updated transition between energy modes data.

Updated power management data.

Updated GPIO data.

Updated LFRCO, HFRCO and ULFRCO data.

Updated ADC data.

Updated DAC data.

Updated OPAMP data.

Updated ACMP data.

Updated VCMP data.

7.2 Revision 1.31

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.3 Revision 1.30

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Added the USB bootloader information.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

List of Figures

2.1. Block Diagram	3
2.2. EFM32WG332 Memory Map with largest RAM and Flash sizes	9
3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz	13
3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz	13
3.3. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21MHz	14
3.4. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14MHz	14
3.5. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11MHz	15
3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6MHz	15
3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 1.2MHz	16
3.8. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.	16
3.9. EM3 current consumption.	17
3.10. EM4 current consumption.	17
3.11. Typical Low-Level Output Current, 2V Supply Voltage	21
3.12. Typical High-Level Output Current, 2V Supply Voltage	22
3.13. Typical Low-Level Output Current, 3V Supply Voltage	23
3.14. Typical High-Level Output Current, 3V Supply Voltage	24
3.15. Typical Low-Level Output Current, 3.8V Supply Voltage	25
3.16. Typical High-Level Output Current, 3.8V Supply Voltage	26
3.17. Calibrated LFRCO Frequency vs Temperature and Supply Voltage	28
3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature	29
3.19. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature	30
3.20. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature	30
3.21. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature	30
3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature	31
3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature	31
3.24. Integral Non-Linearity (INL)	37
3.25. Differential Non-Linearity (DNL)	37
3.26. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C	38
3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C	39
3.28. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C	40
3.29. ADC Absolute Offset, Common Mode = Vdd / 2	41
3.30. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V	41
3.31. ADC Temperature sensor readout	42
3.32. OPAMP Common Mode Rejection Ratio	45
3.33. OPAMP Positive Power Supply Rejection Ratio	45
3.34. OPAMP Negative Power Supply Rejection Ratio	46
3.35. OPAMP Voltage Noise Spectral Density (Unity Gain) V _{out} =1V	46
3.36. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)	46
3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1	48
3.38. SPI Master Timing	51
3.39. SPI Slave Timing	52
4.1. EFM32WG332 Pinout (top view, not to scale)	54
4.2. Opamp Pinout	61
4.3. TQFP64	62
5.1. TQFP64 PCB Land Pattern	64
5.2. TQFP64 PCB Solder Mask	65
5.3. TQFP64 PCB Stencil Design	66
6.1. Example Chip Marking (top view)	67

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